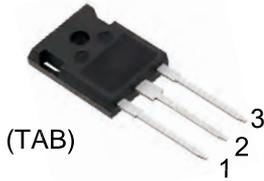


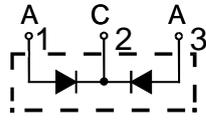
# MUR6040PT, MUR6060PT

## Ultra Fast Recovery Diodes

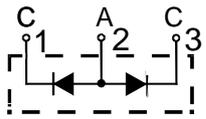


(TAB)

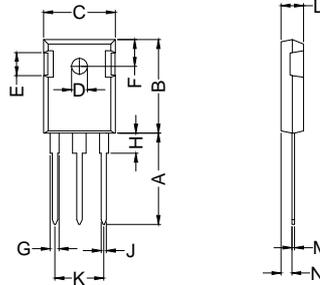
**MUR6060PT**



**MUR6060PA**



Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.620	0.640
∅D	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.30	0.213	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.50	0.150	0.177
J	1.00	1.40	0.039	0.055
K	10.80	11.10	0.425	0.437
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.059	0.098

A=Anode, C=Cathode, TAB=Cathode

	$V_{RSM}$ V	$V_{RRM}$ V
<b>MUR6040PT(PD/PA)</b>	400	400
<b>MUR6060PT(PD/PA)</b>	600	600

Symbol	Test Conditions	Maximum Ratings	Unit
$I_{FRMS}$	$T_{VJ}=T_{VJM}$	50	A
$I_{FAVM}$	$T_C=85^{\circ}C$ ; rectangular, $d=0.5$	2X37	
$I_{FRM}$	$t_p < 10\mu s$ ; rep. rating, pulse width limited by $T_{VJM}$	375	
$I_{FSM}$	$T_{VJ}=45^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	A
	$T_{VJ}=150^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	
$I^2t$	$T_{VJ}=45^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	$A^2s$
	$T_{VJ}=150^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	
$T_{VJ}$ $T_{VJM}$ $T_{stg}$		-40...+150 150 -40...+150	$^{\circ}C$
$P_{tot}$	$T_C=25^{\circ}C$	125	W
$M_d$	Mounting torque	0.8...1.2	Nm
Weight	typical	6	g



**Sirectifier®**

# MUR6040PT, MUR6060PT

## Ultra Fast Recovery Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I <sub>R</sub>	T <sub>VJ</sub> =25°C; V <sub>R</sub> =V <sub>RRM</sub>		100	uA
	T <sub>VJ</sub> =25°C; V <sub>R</sub> =0.8·V <sub>RRM</sub>		50	uA
	T <sub>VJ</sub> =125°C; V <sub>R</sub> =0.8·V <sub>RRM</sub>		7	mA
V <sub>F</sub>	I <sub>F</sub> =37A; T <sub>VJ</sub> =150°C		1.4	V
	T <sub>VJ</sub> =25°C		1.6	
V <sub>TO</sub>	For power-loss calculations only		1.01	V
r <sub>T</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>		7.1	mΩ
R <sub>thJC</sub> R <sub>thCK</sub> R <sub>thJA</sub>		0.25	1	K/W
			70	
t <sub>tr</sub>	I <sub>F</sub> =1A; -di/dt=100A/us; V <sub>R</sub> =30V; T <sub>VJ</sub> =25°C	35	50	ns
I <sub>RM</sub>	V <sub>R</sub> =350V; I <sub>F</sub> =30A; -di <sub>F</sub> /dt=240A/us; L<=0.05uH; T <sub>VJ</sub> =100°C	10	11	A

### FEATURES

- \* International standard package JEDEC TO-247AD
- \* Glass passivated chips
- \* Very short recovery time
- \* Extremely low switching losses
- \* Low I<sub>RM</sub>-values
- \* Soft recovery behaviour
- \* RoHS compliant

### APPLICATIONS

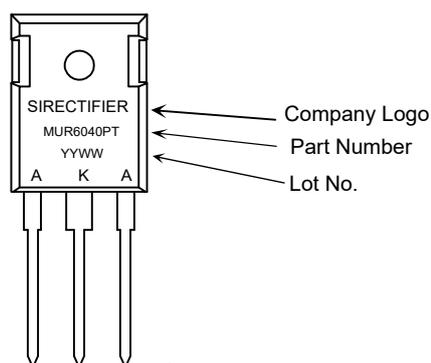
- \* Rectifiers in switch mode power supplies (SMPS)
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses
- \* Operating at lower temperature or space saving by reduced cooling

### Marking

(TO-247AD)



### Ordering Information

Part Number	Package	Shipping	Marking Code
MUR6040PT	TO-247AD	30pcs / Tube	MUR6040PT

# MUR6040PT, MUR6060PT

## Ultra Fast Recovery Diodes

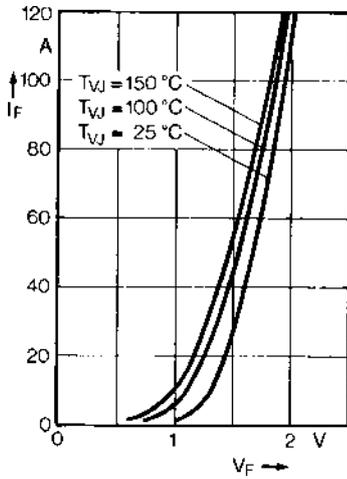


Fig. 1 Forward current versus voltage drop.

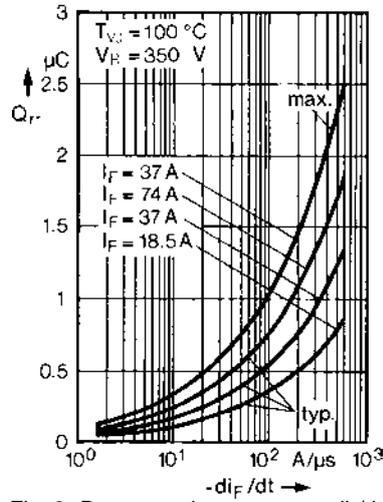


Fig. 2 Recovery charge versus  $-di_F/dt$ .

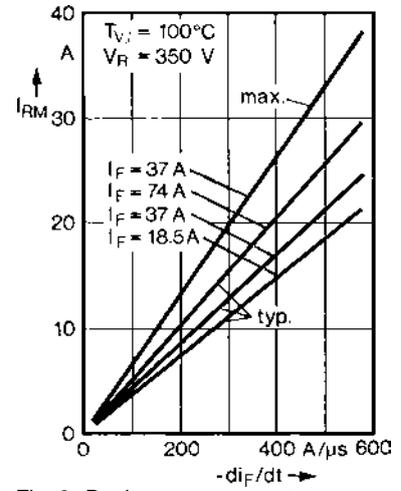


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

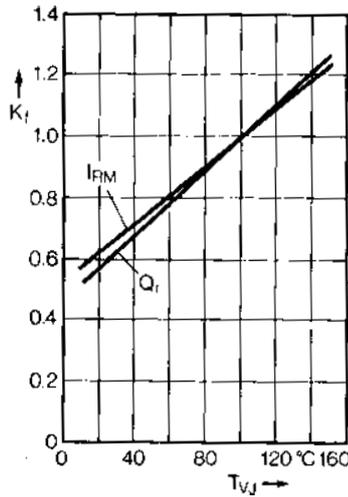


Fig. 4 Dynamic parameters versus junction temperature.

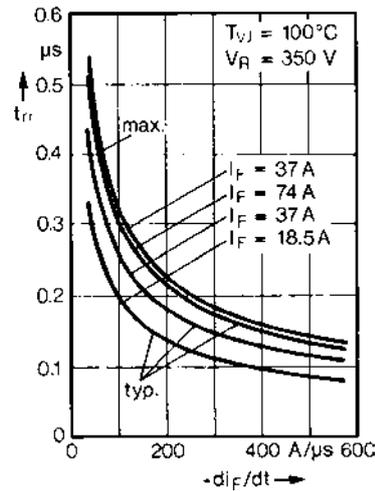


Fig. 5 Recovery time versus  $-di_F/dt$ .

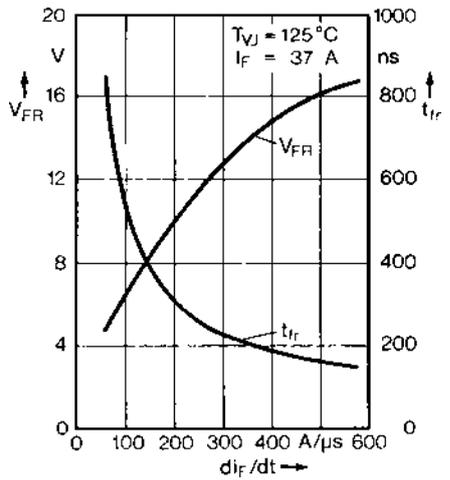


Fig. 6 Peak forward voltage versus  $di_F/dt$ .

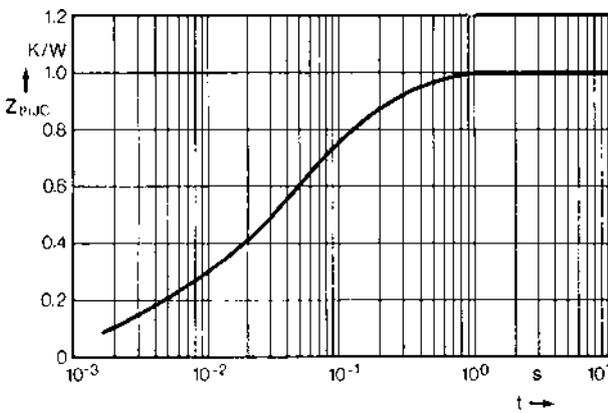


Fig. 7 Transient thermal impedance junction to case.